YJ Planar Schottky Barrier Diode Die Specification

40V 0.5A, 25mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB025L040AS-180A

Main Products Characterstics

- Average forward current: IF(AV) = 0.5 A
- Maximum operating junction temperature: Tj = 125 °C
- Top metal: AL

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

I_F = 0.5 A

Pulse Test: tp = 300 μs, δ ≤ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 10.5 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.